Abstracts

A 6-GHz Four-Stage GaAs MESFET Power Amplifier (Short Papers)

Y. Arai, T. Kouno, T. Horimatsu and H. Komizo. "A 6-GHz Four-Stage GaAs MESFET Power Amplifier (Short Papers)." 1976 Transactions on Microwave Theory and Techniques 24.6 (Jun. 1976 [T-MTT] (Special Issue on Microwave Field-Effect Transistors)): 381-383.

A 6-GHz GaAs MESFET power amplifier with 1-W output power, 26dB gain, and 8-dB noise figure is described. It is a fully integrated four-stage amplifier with an efficiency of 22 percent. The third-order intermodulation product is 31.5 dB below the carrier at an output power of 1 W.

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